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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Willis, Stephen L. ) Group Art Unit 2815  
Appl. No. : 09/552,383 )  
Filed : 04/19/2000 )  
For : CHEMICAL MECHANICAL )  
PLANARIZATION OF )  
CONDUCTIVE MATERIAL )  
Examiner : Diaz, Jose R. )

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed March 14, 2002 (Paper No. 9), please amend the above-captioned application as follows.

IN THE CLAIMS:

Please add new claims as follows:

56. (New) A method of forming a dielectric layer of a first thickness on a semiconductor wafer, the method comprising:  
forming the dielectric layer of the first thickness on the wafer;  
positioning a shield layer on the dielectric layer;  
positioning a sacrificial layer on the shield layer;  
depositing conductive material on the sacrificial layer;